

# IRFP90N20DPbF

HEXFET® Power MOSFET

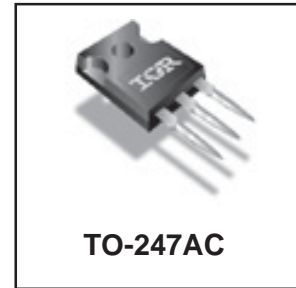
### Applications

- High frequency DC-DC converters
- Lead-Free

<b>V<sub>DSS</sub></b>	<b>R<sub>DS(on) max</sub></b>	<b>I<sub>D</sub></b>
<b>200V</b>	<b>0.023Ω</b>	<b>94A<sup>Ⓓ</sup></b>

### Benefits

- Low Gate-to-Drain Charge to Reduce Switching Losses
- Fully Characterized Capacitance Including Effective C<sub>OSS</sub> to Simplify Design, (See App. Note AN1001)
- Fully Characterized Avalanche Voltage and Current



### Absolute Maximum Ratings

	Parameter	Max.	Units
I <sub>D</sub> @ T <sub>C</sub> = 25°C	Continuous Drain Current, V <sub>GS</sub> @ 10V	94 <sup>Ⓓ</sup>	A
I <sub>D</sub> @ T <sub>C</sub> = 100°C	Continuous Drain Current, V <sub>GS</sub> @ 10V	66	
I <sub>DM</sub>	Pulsed Drain Current <sup>Ⓓ</sup>	380	
P <sub>D</sub> @ T <sub>C</sub> = 25°C	Power Dissipation	580	W
	Linear Derating Factor	3.8	W/°C
V <sub>GS</sub>	Gate-to-Source Voltage	± 30	V
dv/dt	Peak Diode Recovery dv/dt <sup>Ⓓ</sup>	6.7	V/ns
T <sub>J</sub>	Operating Junction and	-55 to + 175	°C
T <sub>STG</sub>	Storage Temperature Range		
	Soldering Temperature, for 10 seconds		
	Mounting torque, 6-32 or M3 screw	10 lbf•in (1.1N•m)	

### Thermal Resistance

	Parameter	Typ.	Max.	Units
R <sub>θJC</sub>	Junction-to-Case	—	0.26	°C/W
R <sub>θCS</sub>	Case-to-Sink, Flat, Greased Surface	0.24	—	
R <sub>θJA</sub>	Junction-to-Ambient	—	40	

Notes <sup>Ⓓ</sup> through <sup>Ⓔ</sup> are on page 8

## Static @ T<sub>J</sub> = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
V <sub>(BR)DSS</sub>	Drain-to-Source Breakdown Voltage	200	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA
ΔV <sub>(BR)DSS/ΔT<sub>J</sub></sub>	Breakdown Voltage Temp. Coefficient	—	0.24	—	V/°C	Reference to 25°C, I <sub>D</sub> = 1mA
R <sub>DS(on)</sub>	Static Drain-to-Source On-Resistance	—	—	0.023	Ω	V <sub>GS</sub> = 10V, I <sub>D</sub> = 56A ④
V <sub>GS(th)</sub>	Gate Threshold Voltage	3.0	—	5.0	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA
I <sub>DSS</sub>	Drain-to-Source Leakage Current	—	—	25	μA	V <sub>DS</sub> = 200V, V <sub>GS</sub> = 0V
		—	—	250		V <sub>DS</sub> = 160V, V <sub>GS</sub> = 0V, T <sub>J</sub> = 150°C
I <sub>GSS</sub>	Gate-to-Source Forward Leakage	—	—	100	nA	V <sub>GS</sub> = 30V
	Gate-to-Source Reverse Leakage	—	—	-100		V <sub>GS</sub> = -30V

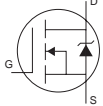
## Dynamic @ T<sub>J</sub> = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
g <sub>fs</sub>	Forward Transconductance	39	—	—	S	V <sub>DS</sub> = 50V, I <sub>D</sub> = 56A
Q <sub>g</sub>	Total Gate Charge	—	180	270	nC	I <sub>D</sub> = 56A V <sub>DS</sub> = 160V V <sub>GS</sub> = 10V, ④
Q <sub>gs</sub>	Gate-to-Source Charge	—	45	67		
Q <sub>gd</sub>	Gate-to-Drain ("Miller") Charge	—	87	130		
t <sub>d(on)</sub>	Turn-On Delay Time	—	23	—	ns	V <sub>DD</sub> = 100V I <sub>D</sub> = 56A R <sub>G</sub> = 1.2Ω V <sub>GS</sub> = 10V ④
t <sub>r</sub>	Rise Time	—	160	—		
t <sub>d(off)</sub>	Turn-Off Delay Time	—	43	—		
t <sub>f</sub>	Fall Time	—	79	—		
C <sub>iss</sub>	Input Capacitance	—	6040	—	pF	V <sub>GS</sub> = 0V V <sub>DS</sub> = 25V f = 1.0MHz
C <sub>oss</sub>	Output Capacitance	—	1070	—		
C <sub>rss</sub>	Reverse Transfer Capacitance	—	170	—		
C <sub>oss</sub>	Output Capacitance	—	8350	—		
C <sub>oss</sub>	Output Capacitance	—	420	—		
C <sub>oss eff.</sub>	Effective Output Capacitance	—	870	—		

## Avalanche Characteristics

	Parameter	Typ.	Max.	Units
E <sub>AS</sub>	Single Pulse Avalanche Energy②	—	1010	mJ
I <sub>AR</sub>	Avalanche Current①	—	56	A
E <sub>AR</sub>	Repetitive Avalanche Energy①	—	58	mJ

## Diode Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I <sub>S</sub>	Continuous Source Current (Body Diode)	—	—	94⑥	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I <sub>SM</sub>	Pulsed Source Current (Body Diode) ①	—	—	380		
V <sub>SD</sub>	Diode Forward Voltage	—	—	1.5	V	T <sub>J</sub> = 25°C, I <sub>S</sub> = 56A, V <sub>GS</sub> = 0V ④
t <sub>rr</sub>	Reverse Recovery Time	—	230	340	ns	T <sub>J</sub> = 25°C, I <sub>F</sub> = 56A
Q <sub>rr</sub>	Reverse Recovery Charge	—	1.9	2.8	μC	di/dt = 100A/μs ④
t <sub>on</sub>	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by L <sub>S</sub> +L <sub>D</sub> )				

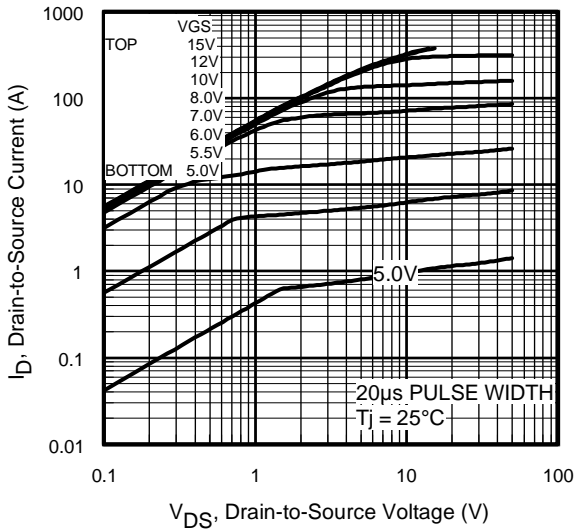


Fig 1. Typical Output Characteristics

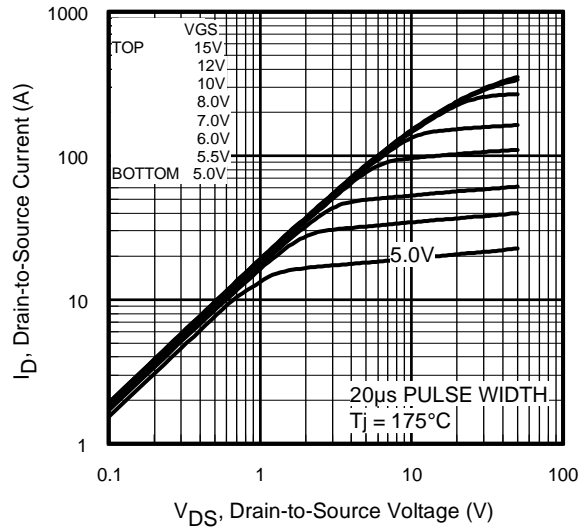


Fig 2. Typical Output Characteristics

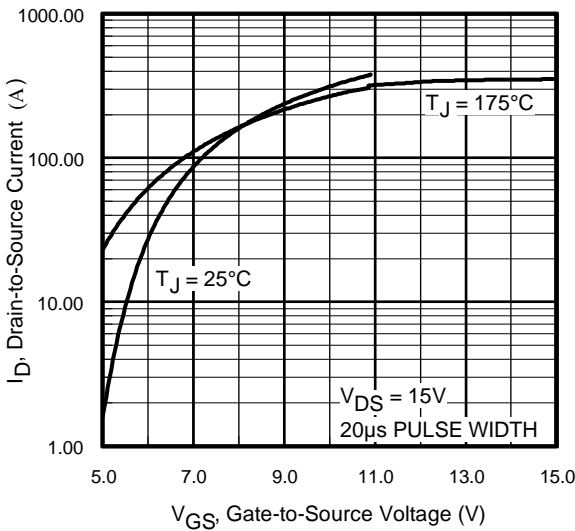


Fig 3. Typical Transfer Characteristics

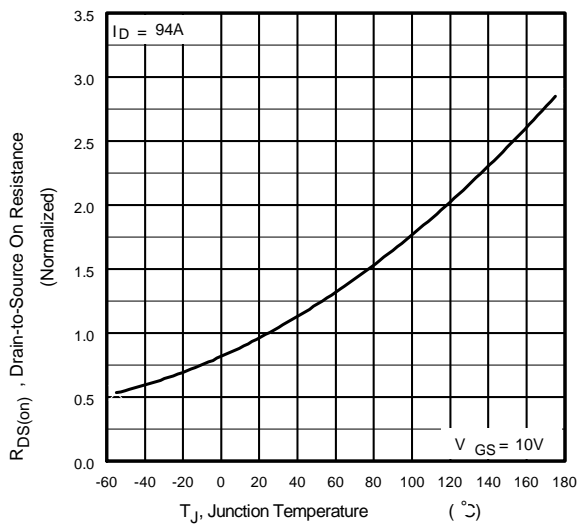
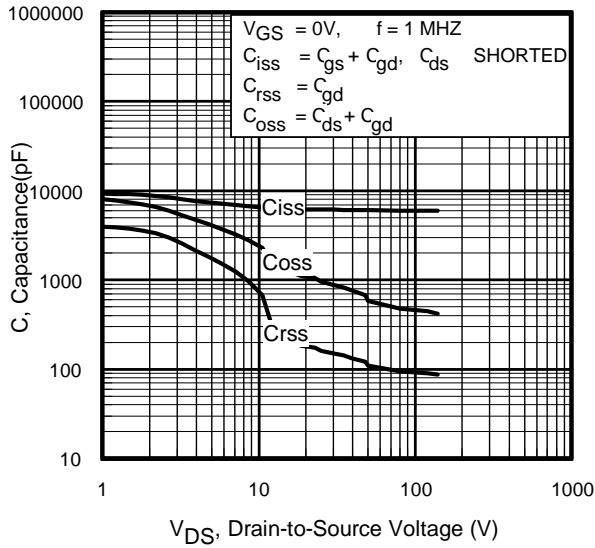
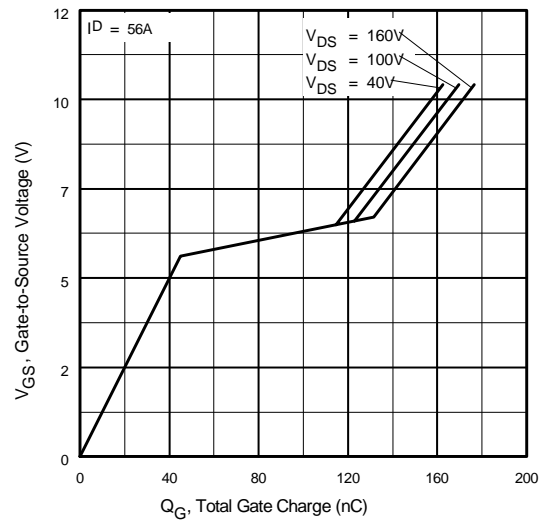


Fig 4. Normalized On-Resistance vs. Temperature

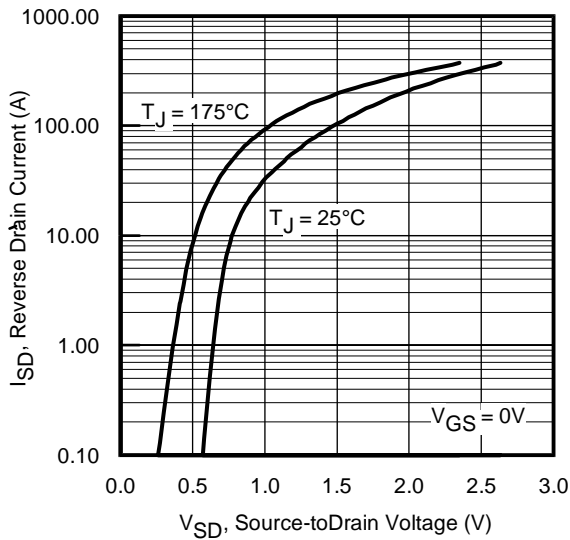
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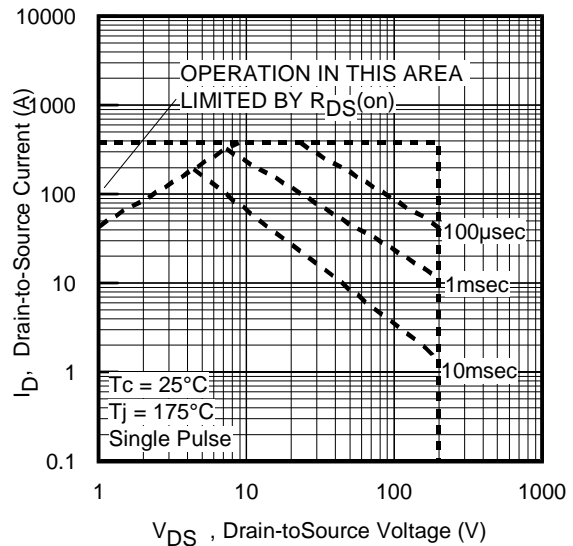
**Fig 5.** Typical Capacitance vs. Drain-to-Source Voltage



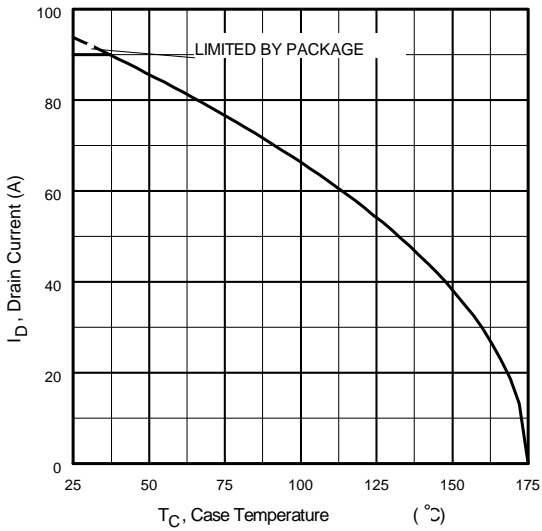
**Fig 6.** Typical Gate Charge vs. Gate-to-Source Voltage



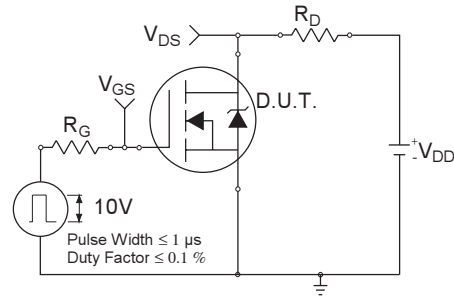
**Fig 7.** Typical Source-Drain Diode Forward Voltage



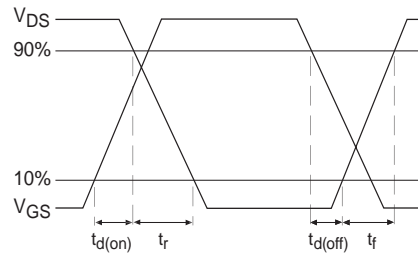
**Fig 8.** Maximum Safe Operating Area



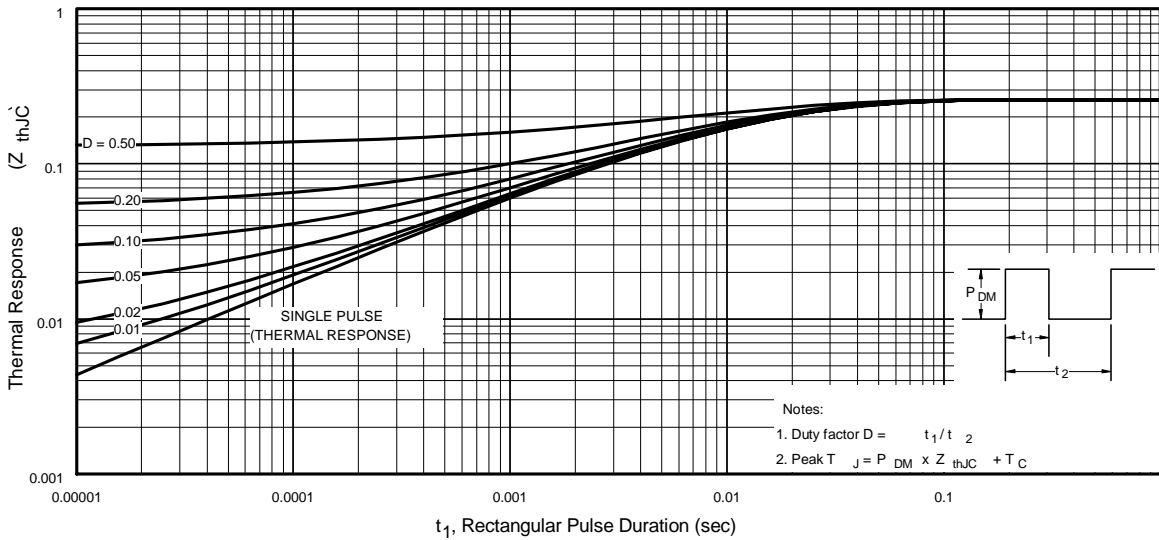
**Fig 9.** Maximum Drain Current vs. Case Temperature



**Fig 10a.** Switching Time Test Circuit



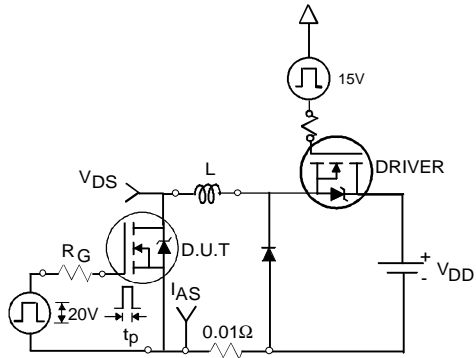
**Fig 10b.** Switching Time Waveforms



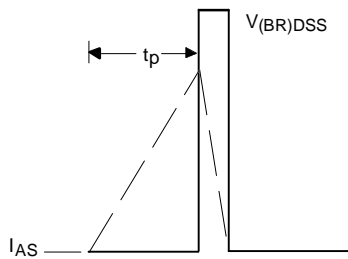
**Fig 11.** Maximum Effective Transient Thermal Impedance, Junction-to-Case

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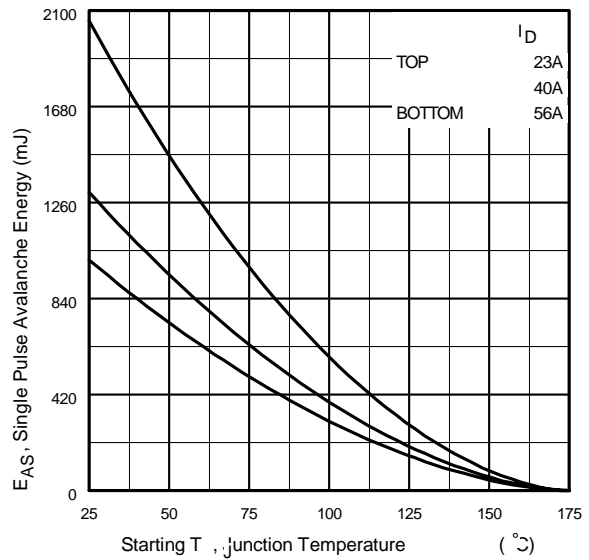
International  
**IR** Rectifier



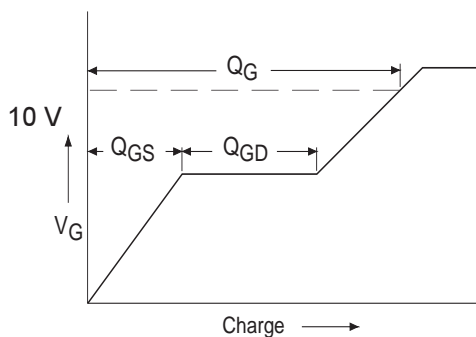
**Fig 12a.** Unclamped Inductive Test Circuit



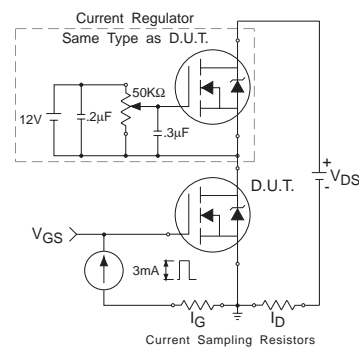
**Fig 12b.** Unclamped Inductive Waveforms



**Fig 12c.** Maximum Avalanche Energy vs. Drain Current

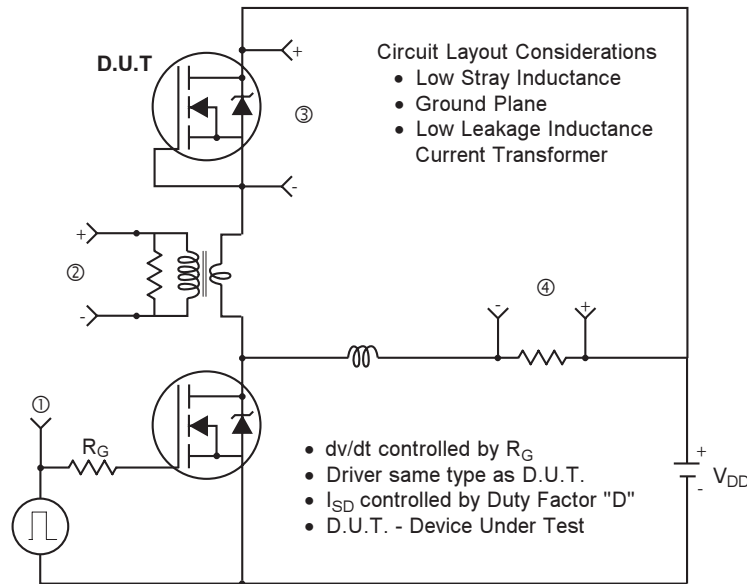


**Fig 13a.** Basic Gate Charge Waveform



**Fig 13b.** Gate Charge Test Circuit

**Peak Diode Recovery dv/dt Test Circuit**



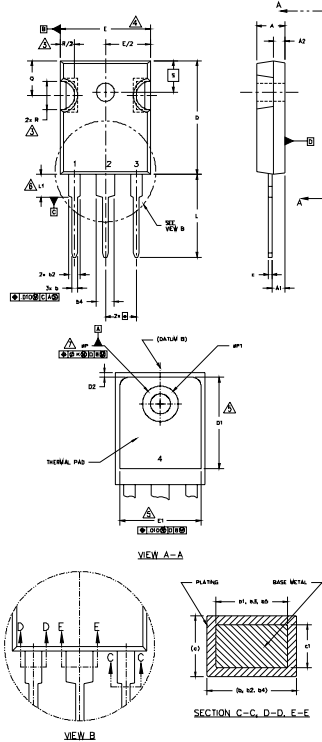
\*  $V_{GS} = 5V$  for Logic Level Devices

**Fig 14.** For N-Channel HEXFET® Power MOSFETs

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TO-247AC Package Outline Dimensions are shown in millimeters (inches)

International  
**IR** Rectifier



NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M 1994.
- DIMENSIONS ARE SHOWN IN INCHES [MILLIMETERS]
- CONTOUR OF SLOT OPTIONAL.
- DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
- THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS D1 & E1.
- LEAD FINISH UNCONTROLLED IN LI.
- #P TO HAVE A MAXIMUM DRAFT ANGLE OF 1.5 ° TO THE TOP OF THE PART WITH A MAXIMUM HOLE DIAMETER OF .154" [3.91]
- OUTLINE CONFORMS TO JEDEC OUTLINE TO-247 WITH THE EXCEPTION OF DIMENSION c.

SYMBOL	INCHES		MILLIMETERS		NOTES
	MIN.	MAX.	MIN.	MAX.	
A	.183	.209	4.65	5.31	LEAD ASSIGNMENTS
A1	.087	.102	2.21	2.59	
A2	.059	.098	1.50	2.49	
b	.039	.055	0.99	1.40	
b1	.039	.053	0.99	1.35	
b2	.065	.094	1.65	2.39	
b3	.065	.092	1.65	2.37	
b4	.102	.135	2.59	3.43	
b5	.102	.133	2.59	3.38	
c	.015	.034	0.38	0.86	
c1	.015	.030	0.38	0.76	LEAD ASSIGNMENTS
D	.776	.815	19.71	20.70	
D1	.515	-	13.08	-	
D2	.020	.030	0.51	0.76	
E	.602	.625	15.29	15.87	
E1	.540	-	13.72	-	
e	215 BSC		5.46 BSC		
e1	.010		2.54		
L	.559	.634	14.20	16.10	
L1	.146	.169	3.71	4.29	
N	3		7.62 BSC		LEAD ASSIGNMENTS
#P	.140	.144	3.56	3.66	
#P1	-	.275	-	6.98	
O	.209	.224	5.31	5.69	
R	.178	.216	4.52	5.49	
S	217 BSC		5.51 BSC		

LEAD ASSIGNMENTS

HEXFET

1 - GATE  
2 - DRAIN  
3 - SOURCE  
4 - DRAIN

IGBTs, CoPACK

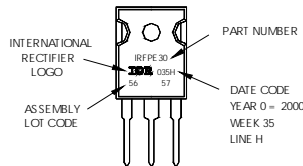
1 - GATE  
2 - COLLECTOR  
3 - EMITTER  
4 - COLLECTOR

DIODES

1 - ANODE/OPEN  
2 - CATHODE  
3 - ANODE

## TO-247AC Part Marking Information

EXAMPLE: THIS IS AN IRFPE30 WITH ASSEMBLY LOT CODE 5657 ASSEMBLED ON WW 35, 2000 IN THE ASSEMBLY LINE "H"  
Note: "P" in assembly line position indicates "Lead-Free"



### Notes:

- Repetitive rating; pulse width limited by max. junction temperature.
- Starting  $T_J = 25^\circ\text{C}$ ,  $L = 0.64\text{mH}$   
 $R_G = 25\Omega$ ,  $I_{AS} = 56\text{A}$ .
- $I_{SD} \leq 56\text{A}$ ,  $di/dt \leq 470\text{A}/\mu\text{s}$ ,  $V_{DD} \leq V_{(BR)DSS}$ ,  
 $T_J \leq 175^\circ\text{C}$
- Pulse width  $\leq 300\mu\text{s}$ ; duty cycle  $\leq 2\%$ .
- $C_{OSS}$  eff. is a fixed capacitance that gives the same charging time as  $C_{OSS}$  while  $V_{DS}$  is rising from 0 to 80%  $V_{DSS}$
- Calculated continuous current based on maximum allowable junction temperature. Package limitation current is 90A.  
Data and specifications subject to change without notice.

This product has been designed and qualified for the Industrial market.

Qualification Standards can be found on IR's Web site.

International  
**IR** Rectifier

IR WORLD HEADQUARTERS: 233 Kansas St., El Segundo, California 90245, USA Tel: (310) 252-7105  
TAC Fax: (310) 252-7903

Visit us at [www.irf.com](http://www.irf.com) for sales contact information.07/04

[www.irf.com](http://www.irf.com)



Note: For the most current drawings please refer to the IR website at:  
<http://www.irf.com/package/>

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